

Features

- SiC MOSFET Technology
- High Speed Switching
- Reduction Of Heat Sink Requirements
- Essentially No Switching Losses
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max^(Note 3): 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.4°C/W

Applications

- Solar Inverters
- Uninterruptible Power Supply
- Photovoltaic Inverter
- Battery Chargers
- Motor Drives

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	650	V
Gate-Source Voltage (Note 4)	V _{GSm}	-10/+25	V
Gate-Source Voltage	V _{GSop}	-5/+20	V
Continuous Drain Current V _{GS} =20V	I _D	107	A
Tc=110°C		72	
Pulsed Drain Current (Note 5)	I _{DM}	305	A
Total Power Dissipation	P _D	375	W
Tc=110°C		162	
Avalanche Energy, Single Pulse	E _{AS}	3.2	J

Note1:Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

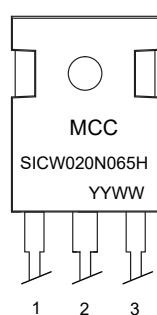
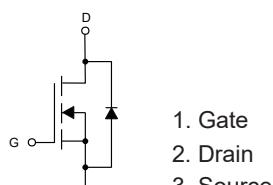
Note2:High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.

Note3:Device in a still air environment with TA=25°C.

Note4:AC f > 1Hz, duty cycle < 1%

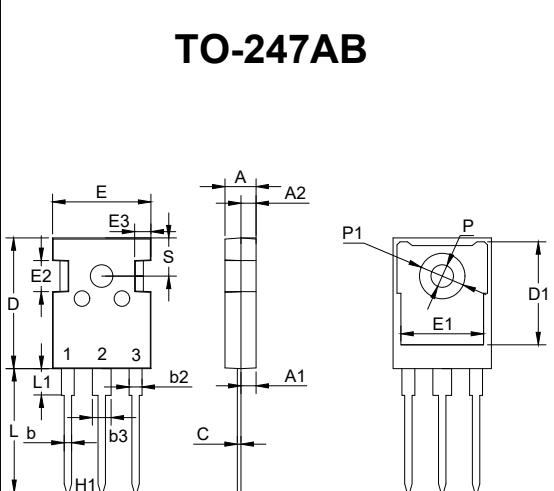
Note5:Pulse Test: Pulse Width Limited by Tjmax.

Internal Structure and Marking Code



Device Code: SICW020N065H
Date Code: YYWW (Year & Week)

SiC N-CHANNEL MOSFET



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.087	0.103	2.21	2.61	
A2	0.073	0.085	1.85	2.15	
b	0.039	0.055	1.00	1.40	
b2	0.075	0.087	1.91	2.21	
C	0.020	0.028	0.50	0.70	
D	0.815	0.839	20.70	21.30	
D1	0.640	0.663	16.25	16.85	
E	0.610	0.634	15.50	16.10	
E1	0.512	0.535	13.00	13.60	
E2	0.189	0.205	4.80	5.20	
E3	0.091	0.106	2.30	2.70	
L	0.772	0.796	19.62	20.22	
L1	-	0.177	-	4.50	
P	0.134	0.150	3.40	3.80	Φ
P1		0.287	-	7.30	Φ
S	0.242		6.15		TYP
H1	0.214		5.44		TYP
b3	0.110	0.126	2.80	3.20	

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS}=0\text{V}, I_D=100\mu\text{A}$	650			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=20\text{V}$			250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650\text{V}, V_{GS}=0\text{V}$			100	μA
Gate-Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=50\text{mA}$	2	3.1	4.5	V
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS}=20\text{V}, I_D=50\text{A}$		20	26	$\text{m}\Omega$
		$V_{GS}=20\text{V}, I_D=50\text{A}, T_j=175^\circ\text{C}$		30		$\text{m}\Omega$
Internal Gate Resistance	R_g	$f=1\text{MHz}, V_{AC}=25\text{mV}$		0.6		Ω
Transconductance	g_{fs}	$V_{DS}=10\text{V}, I_D=60\text{A}$		18.2		s
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=400\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}, V_{AC}=25\text{mV}$		5740		pF
Output Capacitance	C_{oss}			359		
Reverse Transfer Capacitance	C_{rss}			47		
Cross Stored Energy	E_{oss}			34		μJ
Total Gate Charge	Q_g	$V_{DS}=400\text{V}, V_{GS}=-5/+20\text{V}, I_D=50\text{A}$		287		nC
Gate-Source Charge	Q_{gs}			80		
Gate-Drain Charge	Q_{gd}			75		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD}=400\text{V}, V_{GS}=-4/+20\text{V}, R_G=2.7\Omega, I_D=35\text{A}, R_L=11.4\Omega$		29		ns
Rise Time	t_r			51		
Turn-Off Delay Time	$t_{d(\text{off})}$			30		
Fall Time	t_f			16		
Turn-On switching energy	E_{on}	$V_{DS}=400\text{V}, V_{GS}=0/+20\text{V}, R_G=2.7\Omega, I_D=50\text{A}$		61.7		μJ
Turn-Off switching energy	E_{off}			101		
Short-Circuit Withstand Time	t_{sc}	$V_{GS}=0/15\text{V}, V_{DS}=400\text{V}, R_G=100\Omega$		<18		μs
Diode Characteristics						
Continuous Body Diode Current	I_S	$V_{GS}=0\text{V}, T_C=25^\circ\text{C}$		61.5		A
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_{SD}=10\text{A}$		2.9		V
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_{SD}=30\text{A}, V_{DS}=400\text{V}, dI_F/dt=300\text{A}/\mu\text{s}$		77		ns
Reverse Recovery Charge	Q_{rr}			301		nC
Peak Reverse Recovery Current	I_{rrm}			6.9		A

Curve Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

Fig. 1 - Typical Output Characteristic ($T_j=25^\circ\text{C}$)

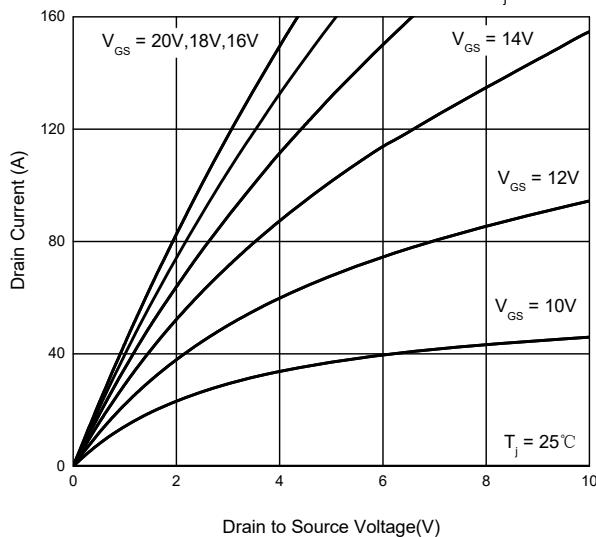


Fig. 2 - Typical Output Characteristic ($T_j=175^\circ\text{C}$)

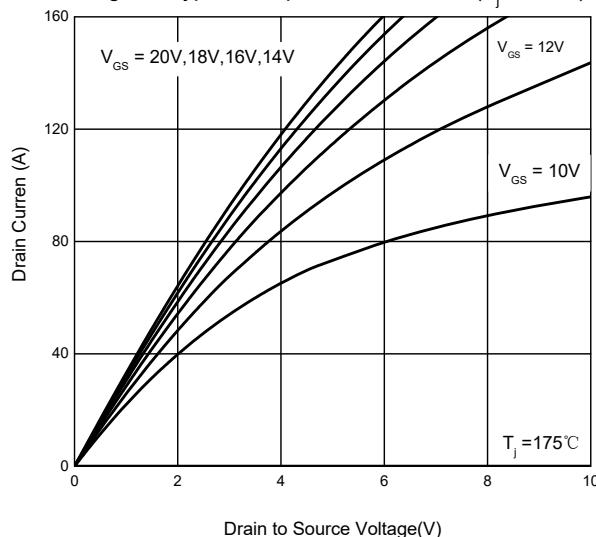


Fig. 3 - On-Resistance vs. Drain Current

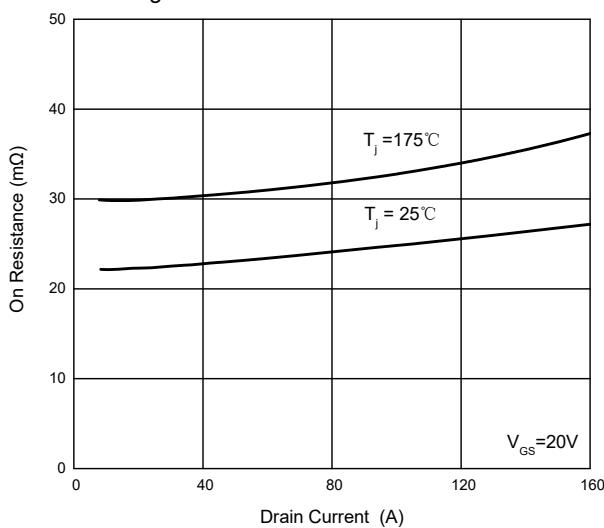


Fig. 4 - Typical Transfer Characteristic

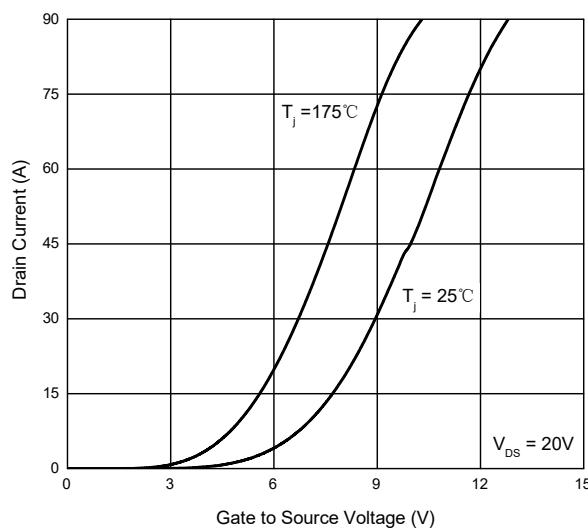


Fig. 5 - On-Resistance vs. Gate Voltage

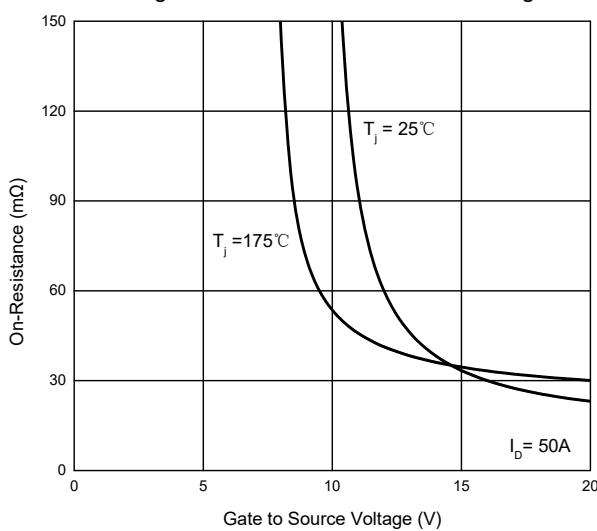
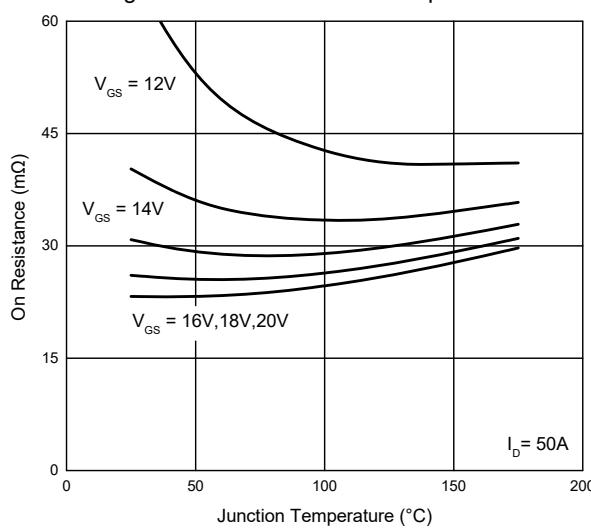


Fig. 6 - On-Resistance vs. Temperature



Curve Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Fig. 7 - Normalized On-Resistance vs. Temperature

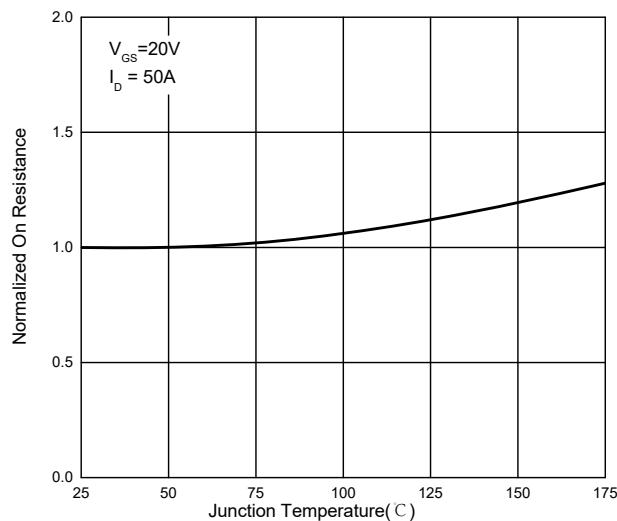


Fig. 8 - Reverse Output Voltage

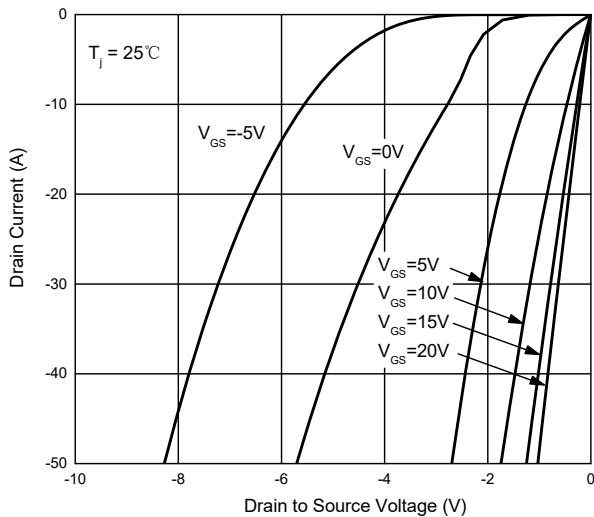


Fig. 9 - Reverse Output Voltage

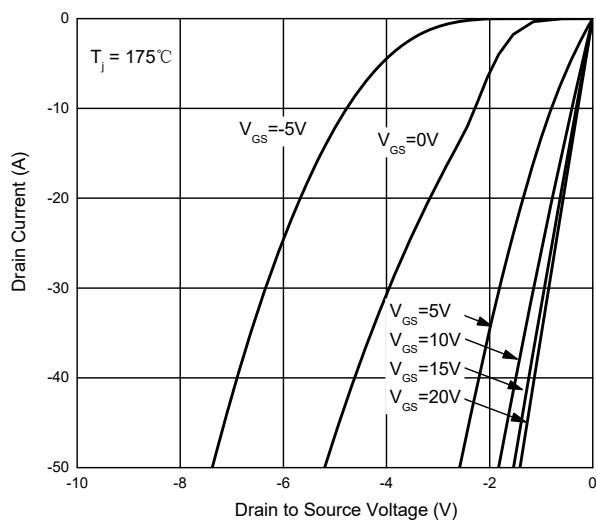


Fig. 10 - Capacitances vs. V_{DS}

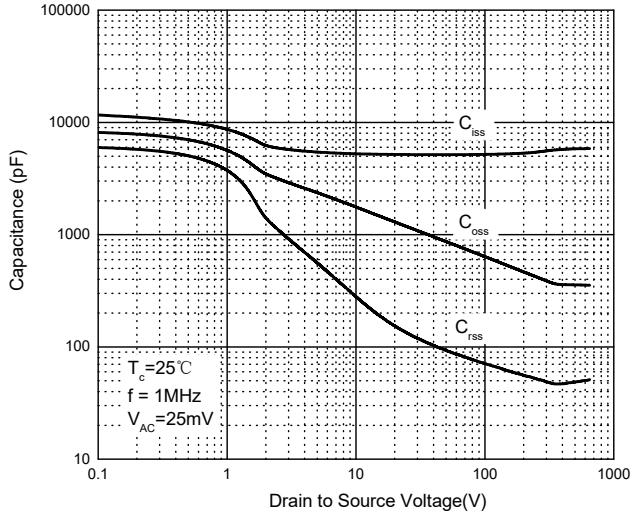


Fig. 11 - Threshold Voltage vs. Temperature

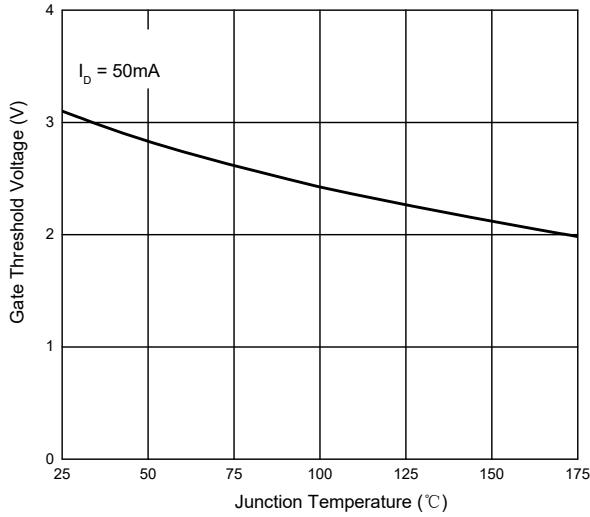
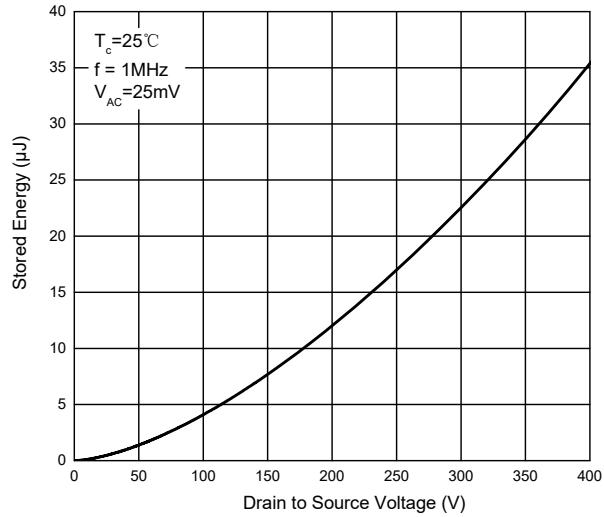


Fig. 12 - Output Capacitor Stored Energy



Curve Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Fig. 13 - Power Derating

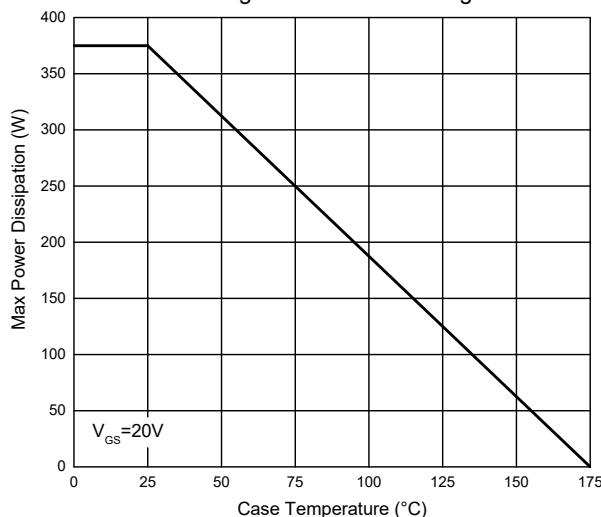


Fig. 14 - Drain Current Derating

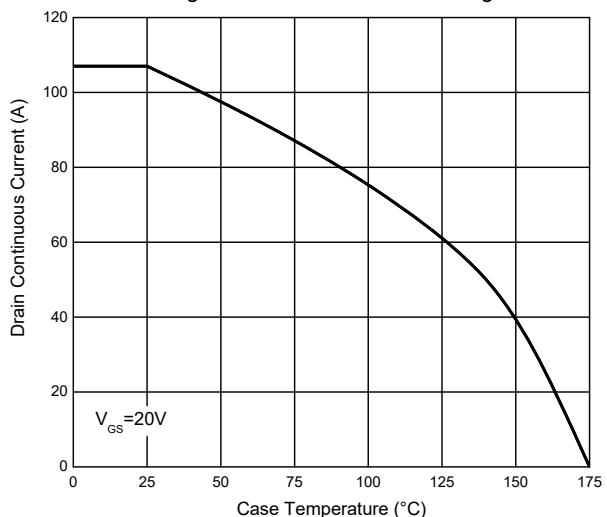


Fig. 15 - Safe Operation Area

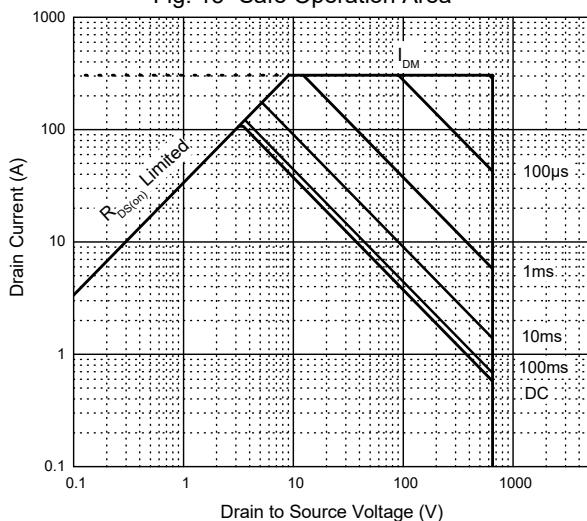


Fig. 17 - Clamped Inductive Switching Energy vs. Drain Current

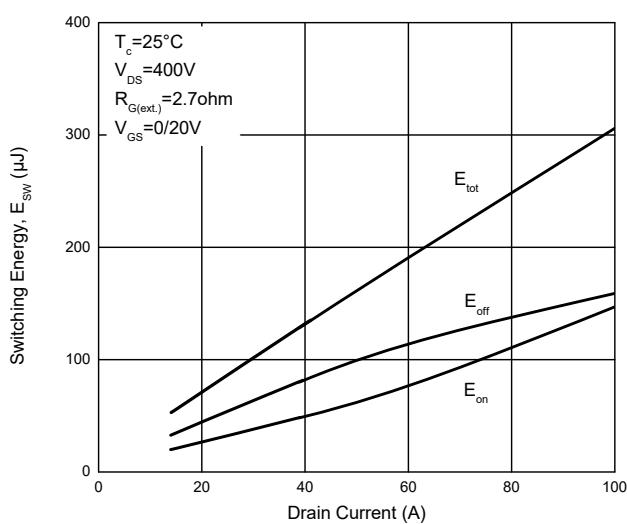


Fig. 16 - Typical Gate Charge

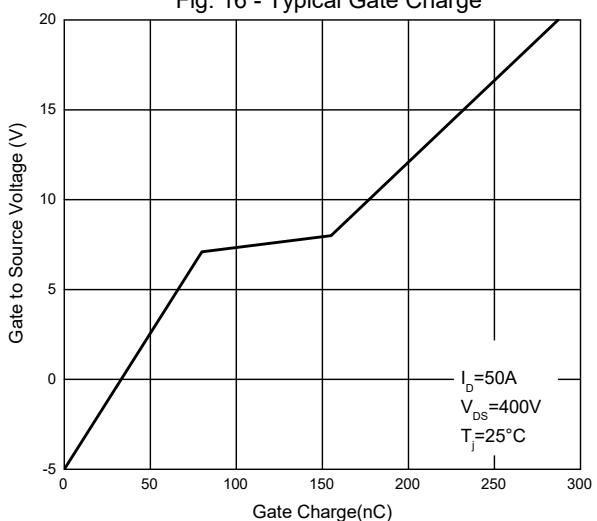
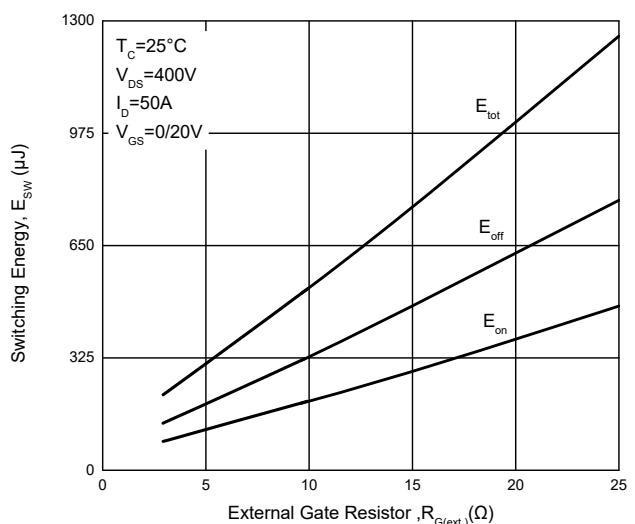
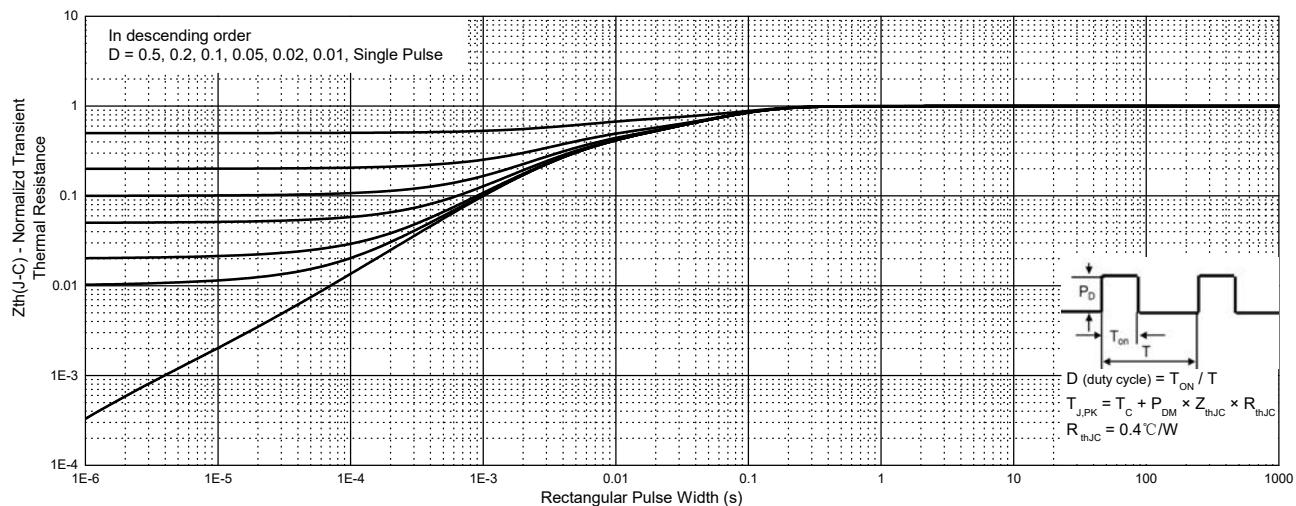


Fig. 18 - Clamped Inductive Switching Energy vs. External Gate Resistor ($R_{G(ext.)}$)



Curve Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Fig.19 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
SICW020N065H-BP	Tube:30pcs/Tube, 1.8K/Ctn;

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